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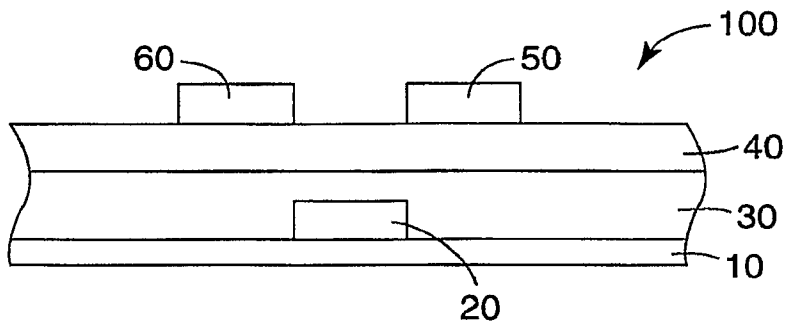
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(54) Title: ALL-INKJET PRINTED THIN FILM TRANSISTOR



(57) Abstract: A method is provided for making a thin film transistor comprising the steps of: providing a substrate; applying a gate electrode ink by inkjet printing; applying a dielectric ink over by inkjet printing; applying a semiconductor ink by inkjet printing; and applying a source and drain electrode ink by inkjet printing. In some embodiments the semiconductor ink comprises a solvent and a semiconducting material comprising: 1-99.9% by weight of a polymer; and 0.1-99% by weight of a functionalized pentacene compound as described herein.

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